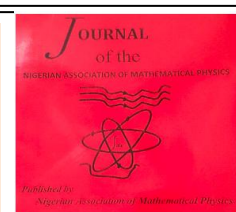


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## ON THE ELECTROLUMINESCENCE, OPTICAL AND ELECTRICAL PROPERTIES OF $\text{TiO}_2/\text{NiO}$ CORE-SHELL THIN FILMS

<sup>1</sup>Daniel U. Onah, <sup>2</sup>John E. Ekpe, <sup>3</sup>Edwin H. Uguru, <sup>4</sup>Rufus O. Ijeh and <sup>5</sup>Stephen Eze

<sup>1</sup>Department of Industrial Physics, Ebonyi State University, Abakaliki – Nigeria

<sup>2</sup>Department of Physics, Alex Ekwueme Federal University, Ndufu Alike-Ikwo (AE-FUNAI)

<sup>3</sup>Department of Industrial Physics/Astronomy, David Umahi Federal University of Health Sciences, Uburu.

<sup>4</sup>Department of Physics, University of Delta, Agbor Delta State.

<sup>5</sup>Department of Physics, FCE (Technical) Ekiadolor Benin City, Nigeria.

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### ABSTRACT

*The electroluminescent properties, some optical and electrical properties of nanocrystalline  $\text{TiO}_2/\text{NiO}$  core-shell thin films were studied and reported in this paper. The study was within the ultraviolet, visible and near infrared regions of electromagnetic spectrum. The films' structural properties, microstructure, optical and electrical properties were analysed using X-ray diffraction, scanning electron microscope [SEM] analysis, spectrophotometric analysis and the four-point probe. In this paper, the dependence of reflectance, extinction coefficients and resistivity of the thin film samples on the annealing temperatures were particularly highlighted. Increasing the annealing temperatures from 373K to 673K resulted in the decrease in resistivity from  $1.683 \times 10^4 \Omega\text{m}$  to  $1.121 \times 10^4 \Omega\text{m}$ . The films have low reflectance values ranging from 10% to 20%, and the increase in the annealing temperatures increased and enhanced the electroluminescent property of the studied core-shell thin films.*

## 1. INTRODUCTION

Titanium dioxide [ $\text{TiO}_2$ ] thin film is a very important functional material and its preparation, performance and application have become hot topics in recent years [1]. Due to the smaller size of primary particles and higher surface area,  $\text{TiO}_2$  as a nanomaterial allows the manufacture of various catalysts of enhanced activity [2]. Numerous applications of  $\text{TiO}_2$  include photonic devices [3], dye-sensitized solar cell [4], photoactivated catalysts and UV absorbers [2,5] and insulator gate in metal-insulator – semiconductor [MIS] structures [6]. According to the United Nations' [UN] Globally Harmonized System of classification and labelling of chemicals [GHS].  $\text{TiO}_2$  is not hazardous. Also as nanomaterials,  $\text{TiO}_2$  is more effective as UV absorbers or photocatalysts and its transparency makes it a suitable material as a protective ingredient for sunscreens [7].

\*Corresponding author: DANIEL U. ONAH

E-mail address: [daniel.onah@ebsu.edu.ng](mailto:daniel.onah@ebsu.edu.ng)

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The use of nanocrystalline  $\text{TiO}_2$  as an electron accepting electrode for dye-sensitized solar cells has shown an overall power conversion efficiency as high as 10% [8]. Several and simple deposition techniques such as; chemical bath deposition [CBD] technique, site – selective deposition [SSD] method, RF magnetron sputtering, Sol-gel methods and direct current [d.c] magnetron sputtering etc, have been used to deposit metal oxide thin films of  $\text{TiO}_2$ ,  $\text{NiO}$ ,  $\text{ZnO}$ ,  $\text{CoO}$  and  $\text{Co}_3\text{O}_4$  etc [1, 5, 9 – 12].

Nickel oxide [ $\text{NiO}$ ] is an attractive material due to its excellent chemical stability as well as optical, electrical, magnetic and catalytic properties [10, 13].  $\text{NiO}$  thin films have been shown to be very useful as optically active counter electrodes for window layer applications and the optical quality of  $\text{NiO}$  thin films is improved by annealing [14].  $\text{NiO}$  thin films are very suitable as positive electrodes and can be used in asymmetric devices with cobalt oxide thin films [15, 16]. Study of optical and electrical properties of  $\text{NiO}$  thin films has shown that  $\text{NiO}$  has higher absorbance of 77.7% and electrical conductivity of  $1.3 \times 10^{-5} (\Omega\text{cm})^{-1}$  [17].

A relatively new and novel dimension in thin film technology is the development of core-shell thin films for various device applications. Synthesis of  $\text{Ag@SnO}$  core-shell structure nanoparticle thin films has been carried out using a soft-chemical technique in aqueous phase at  $60^\circ\text{C}$  [18].  $\text{ZnO/CdSe}$  core-shell nanorod array films synthesized via a two-step method have been used as solar cell photoanodes [19]. However, reports on metal oxides core-shell thin films have not been made extensively in the literature.

Electroluminescence is a process that converts an electrical input into a light output and it was first discovered by Round around 1907 in a silicon carbide substrate contact [20]. Direct and wide energy gap materials are good candidates for efficient electroluminescence, and  $\text{ZnO}$ : In thin film with a direct band gap of 3.44eV has been reported to be a good material for electroluminescent devices [20, 21]. Thin film electroluminescent [TFEL] can provide light sources for a variety of purposes in which planar or linear sources of lithographically determined dimensions of high radiance are wanted [22]. The use of glass substrates facilitates high temperature processing that optimized the luminescent properties of the thin films [23]. The electroluminescent properties, dependence of reflectance, extinction coefficients and resistivity of  $\text{TiO}_2/\text{NiO}$  core-shell thin films on the annealing temperatures are particularly emphasized and highlighted in this paper.

The Objectives of this study are; to:

- (i) deposit core-shell thin films of  $\text{TiO}_2/\text{NiO}$  on Sail Brand Microscopic slides Cat. No. 7102 of  $76.2 \times 25.4 \times 1.1\text{mm}$ , using chemical bath deposition [CBD] technique.
- (ii) investigate the electroluminescent properties and
- (iii) highlight the dependence of reflectance, extinction coefficients and resistivity of the thin films on the annealing temperatures.

## 2.0 MATERIALS AND METHODS

The materials used for the synthesis of the core [ $\text{TiO}_2$ ] include titanium trichloride [ $\text{TiCl}_3$ ], sodium hydroxide pellets [ $\text{NaOH}$ ], polyvinyl alcohol [PVA] while the shell [ $\text{NiO}$ ] was synthesized using nickel sulphate [ $\text{NiSO}_4$ ], potassium chloride [ $\text{KCl}$ ], water [ $\text{H}_2\text{O}$ ] and ammonia [ $\text{NH}_3$ ]. Chemical bath deposition [CBD] technique was used in this experiment because it is highly specific, cost effective and convenient. More experimental details have been reported, showing that  $\text{TiO}_2/\text{NiO}$  thin film samples have direct wide band gaps ranging from 2.3eV to 2.5eV [24].

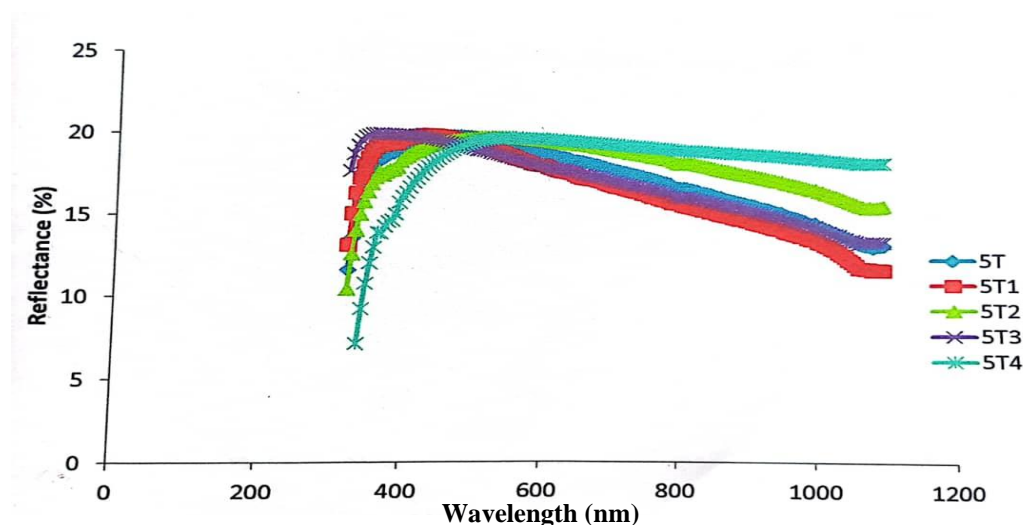
## 2.1 Thin Films Characterization

The thin films' structural properties, morphology, optical and electrical properties were analysed using X-ray diffraction, scanning electron microscope [SEM] analysis, spectrophotometric analysis and the four-point probe. The electroluminescent properties, some optical and electrical properties reported in this paper were studied in the temperature range from 373 – 673K for TiO<sub>2</sub>/NiO core-shell thin films and reported in the wavelength range from 200 – 1200 nm of the electromagnetic spectrum. Four samples of the films were annealed before characterization. These samples are labelled 5T<sub>1</sub> – 5T<sub>4</sub> respectively while the sample not annealed [as – deposited] is labelled 5T.

## RESULTS AND DISCUSSION

### 3.1 Reflectance [R]

The reflectance of a thin film is the ratio of the light reflected to incident light energy. The total energy reflected, absorbed and transmitted per unit area per second is equal to the incident energy in the same time over the same area. It is an intrinsic optical property of thin films and can be used to determine other properties of thin films such as colour, transparency and dielectric or polarization characteristics [24]. Figure 1, shows the graphs of reflectance against wavelength for the thin film samples.

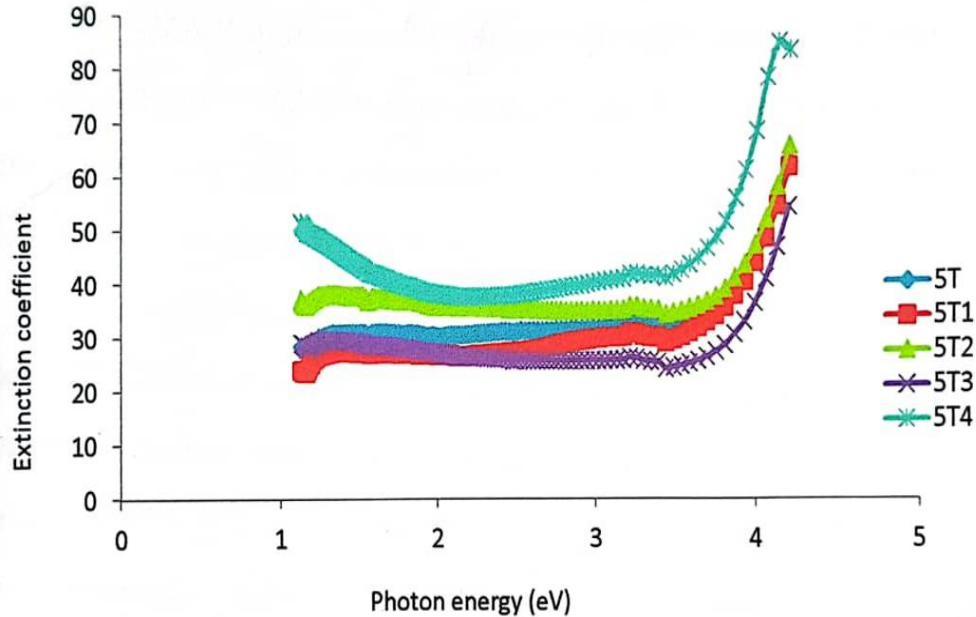


**Fig. 1: Reflectance vs. wavelength for TiO<sub>2</sub>/NiO core-shell thin films**

It can be observed in Fig. 1, that the values of reflectance for the thin film samples increased sharply from 10% to 20% for the as-deposited sample [5T] and also for the samples annealed at 373K [5T<sub>1</sub>] and 573K [5T<sub>3</sub>] respectively. This occurred within the NIR [300 nm] and visible [400 nm] regions. Beyond 400nm [401 – 1100 nm], the reflectance of these film samples decreased gradually. The sample annealed at 673K [5T<sub>4</sub>] has its reflectance increased from 6% to 20% within the ultraviolet to visible regions [270 – 500 nm]. The maximum value of reflectance [20%] for this sample remained constant in the wavelength range from 500 – 1100 nm [i.e within the visible and infrared regions]. The low values of reflectance [6 – 20%] could enhance both the short- circuit current and open circuit voltage of TiO<sub>2</sub>/NiO core-shell thin films as photovoltaic materials like solar cells, regulate light transmission and temperature, display technologies and energy efficiency [25].

### 3.2 Extinction Coefficients

Extinction coefficient is a macroscopic constant though it is really not at all constant because it varies with frequency or photon energy [26]. The extinction coefficients of these thin film samples were determined using transmittance and reflectance measurements. The graphs of extinction coefficients of the film samples versus photon energy are shown in Figure 2.



**Fig. 2: Extinction coefficient vs. photon energy for TiO<sub>2</sub>/NiO core-shell thin films**

From Fig. 2, the sample annealed at 673K, [5T<sub>4</sub>] has the highest value of extinction coefficient which decreased from 50 to 40 between 1 to 2eV. Between 2 to 3.5eV, the value of extinction coefficient 40, remained constant but sharply increased to a maximum value of 80 at a photon energy greater than 3.5 eV. The sample annealed at 573K [5T<sub>3</sub>] has lowest value 25, of extinction coefficient which remained constant between 1 – 3.5eV of photon energy. The value increased to 50 in the energy range from 3.5 – 4.0eV. The as – deposited sample [5T] and the samples annealed at 373 – 473K temperatures, have nearly the same extinction coefficient which increased from 30 to a maximum value of 55 each, between 3.5 – 4.0eV of photon energy. With these trends, the values of extinction coefficients of the thin film samples cannot be said to be explicit functions of the annealing temperatures. This result does not agree with the one obtained for variation of extinction coefficient with annealing temperature for ZnO: Al thin films [27].

### 3.3 Electrical Resistivity [ $\rho$ ]

The electrical resistivity of TiO<sub>2</sub>/NiO core-shell thin films was studied in air by using QUARDPRO 301 – auto calculating four-point probe. Four-point probe is the most common method for measuring resistivity. The values of the resistivity of the thin film samples at different annealing temperatures are shown in table 1.

**Table 1: Resistivity value of TiO<sub>2</sub>/NiO core-shell thin films at different annealing temperatures**

Film sample	Annealing temperature [K]	Resistivity $\rho$ [ $\Omega\text{m}$ ]
5T	Nil (as-deposited)	$1.683 \times 10^4$
5T <sub>1</sub>	373	$1.465 \times 10^4$

5T <sub>2</sub>	473	1.203 x 10 <sup>4</sup>
5T <sub>3</sub>	573	1.156 x 10 <sup>4</sup>
5T <sub>4</sub>	673	1.121 x 10 <sup>4</sup>

Comparing the values of the resistivity of the studied thin film samples, the values of  $\rho$  decreased with the increase in the annealing temperatures as shown in table 1. This clearly indicates the semi-conducting nature of the thin films. Increase in the post-deposition heat treatment of the films resulted to better crystallization, greater grain size of the thin films and decrease defects density so that the resistivity of thin films decreased. Similar results were reported on the studies of electrical properties of other thin films [14, 28, 29].

### 3.4 Electroluminescent Property

Chemical bath deposition technique is a low temperature method of synthesizing a high luminance thin film electroluminescent [TFEL] device on [Sail Brand] microscopic slides Cat. No. 7102 of 76.2 x 25.4 x 1.1mm. Post deposition sintering at the temperature ranging from 373K to 673K was used to enhance electroluminescent emission of TiO<sub>2</sub>/NiO core-shell thin films since high temperature increased the density of the active luminescent centres of the thin films [24, 30]. The relatively high bandwidth or energy gap [direct,  $E_g > 2.0\text{eV}$ ], simple fabrication, low cost, low deposition temperature dependence, high mechanical stability [23], are some of the properties of TiO/NiO core-shell thin films that make them suitable light sources [24, 30, 31].

### Conclusions

We have deposited and characterized the core-shell thin films of TiO<sub>3</sub>/NiO using the chemical bath deposition [CBD] technique. Four samples of the thin film were annealed or subjected to post – deposition sintering. The thin films have low reflectance ranging from 10% to a maximum of 20%. The extinction coefficients of the thin films were not explicit functions of the annealing temperatures. The resistivity of the films decreased with increase in the post deposition heat treatment or annealing temperatures. Annealing temperature increased and enhanced the electroluminescent property of the core-shell thin films of TiO<sub>2</sub>/NiO.

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### Conflict of Interest

The Authors hereby declare no conflict of interest.

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